

N-Channel MOSFET Transistor

IRF634

DESCRIPTION

- Drain Current $-I_D = 8.1A @ T_C = 25^\circ C$
- Drain Source Voltage
: $V_{DSS} = 250V(\text{Min})$
- Static Drain-Source On-Resistance
: $R_{DS(\text{on})} = 0.45 \Omega (\text{Max})$
- Fast Switching Speed
- Low Drive Requirement

APPLICATIONS

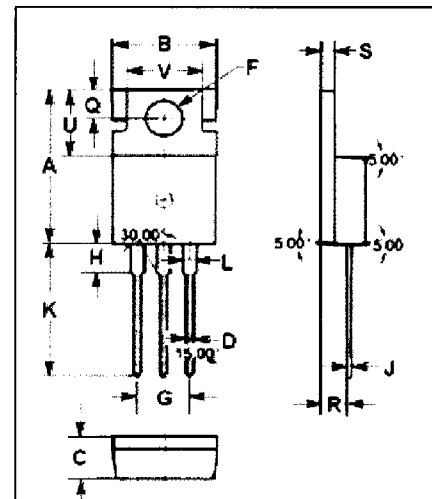
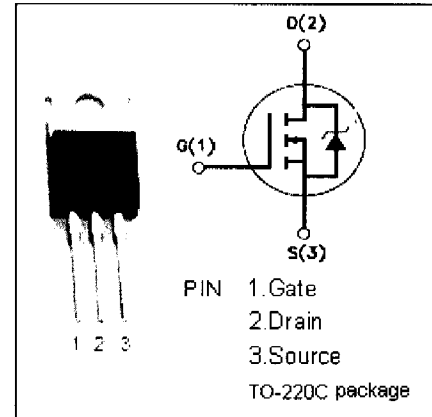
- High current , high speed switching
- Switch mode power supplies
- DC-DC converters for telecom, industrial, and lighting equipment ideal for monitor's B+ function

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	250	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $T_C = 25^\circ C$	8.1	A
P_{tot}	Total Dissipation@ $T_C = 25^\circ C$	74	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-65~150	$^\circ C$

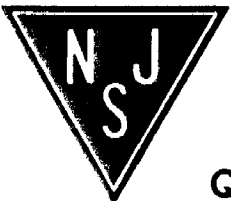
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1.56	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	62.5	$^\circ C/W$



DIM	mm	
	MIN	MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

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• ELECTRICAL CHARACTERISTICS (T_C=25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 0.25mA	250		V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 0.25mA	2	4	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 10V; I _D = 5.1A		0.45	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±20V; V _{DS} = 0		±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 250V; V _{GS} = 0		25	uA
V _{SD}	Diode Forward Voltage	I _F = 8.1A; V _{GS} = 0		2.0	V